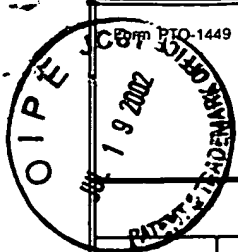
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		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.		
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U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>[Signature]</i>	AA	5,972,800	10/99	Hasegawa				
	AB	6,146,948	11/00	Wu et al.				
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	AM						
	AN						
	AO						
	AP						
	AQ						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		Liu, C.T. et al., "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies", IEEE 1998, pp. 589-592.
	AS		
	AT		

EXAMINER

DATE CONSIDERED

11/2/02

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U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<i>SLK</i>	AM	WO 96/39713	12/96	PCT			
	AN						
	AO						
	AP						
	AQ						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

<i>SLK</i>	AR		Ko, L. et al., "The Effect of Nitrogen Incorporation into the Gate Oxide By Using Shallow Implantation of Nitrogen and Drive-In Process", IEEE 1996, pp. 32-35.
<i>SLK</i>	AS		Doyle, B. et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing", IEEE Vol. 16 (7), July 1995, pp. 301-302.
<i>SLK</i>	AT		Kuroi, T. et al., "The Effects of Nitrogen Implantation Into P+Poly-Silicon Gate on Gate Oxide Properties", 1994 Sympos. on VLSI Technology Digest of Technical Papers, IEEE 1994, pp. 107-108.

EXAMINER

DATE CONSIDERED

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